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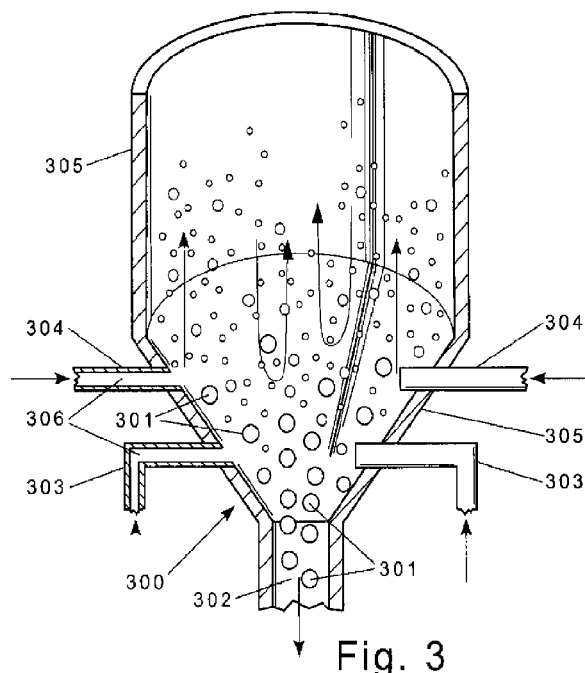
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(54) Title: SILICON PRODUCTION WITH A FLUIDIZED BED REACTOR UTILIZING TETRACHLOROSILANE TO REDUCE WALL DEPOSITION



(57) Abstract: Silicon deposits are suppressed at the wall of a fluidized bed reactor by a process in which an etching gas is fed near the wall of the reactor. The etching gas includes tetrachlorosilane. A Siemens reactor may be integrated into the process such that the vent gas from the Siemens reactor is used to form a feed gas and/or etching gas fed to the fluidized bed reactor.

**Declarations under Rule 4.17:**

- *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))*
- *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*
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